TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT20J321

High Power Switching Applications

Fast Switching Applications

- Fourth-generation IGBT
- Enhancement mode type
- Fast switching (FS): Operating frequency up to 50 kHz (reference) High speed: $t_f = 0.04 \mu s$ (typ.)

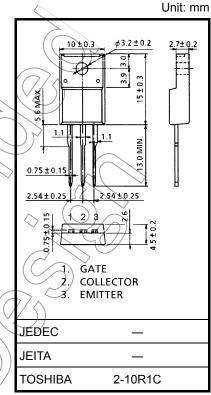
Low switching loss : $E_{on} = 0.40 \text{ mJ (typ.)}$

 $: E_{off} = 0.43 \text{ mJ (typ.)}$

- Low saturation voltage: VCE (sat) = 2.0 V (typ.)
- FRD included between emitter and collector

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	V	
Gate-emitter voltage		V _{GES}	±20	> v	
Collector current	DC	IC	20	А	
	1 ms	I _{CP}	40		
Emitter-collector forward current	DC	l _F	20	A	
	1 ms	I _{FM}	40		
Collector power dissipation (Tc = 25°C)		Pc	45	W	
Junction temperature		(F)	150	∕ °C	
Storage temperature range		(T _{stg}))	-55 to 150	∫\°C	
				7 7	



Weight: 1.7 g (typ.)

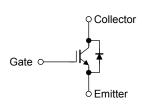
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

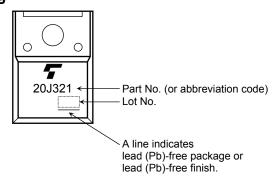
Thermal Characteristics

Characteristics		Symbol	Max	Unit
Thermal resistance (IGBT)	\wedge	Rth (j-c)	2.78	°C/W
Thermal resistance (diode)		Rth (j-c)	4.23	°C/W

Equivalent Circuit



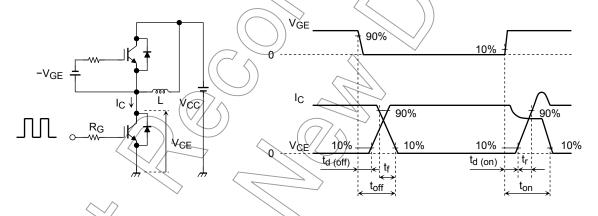
Marking



Electrical Characteristics (Ta = 25°C)

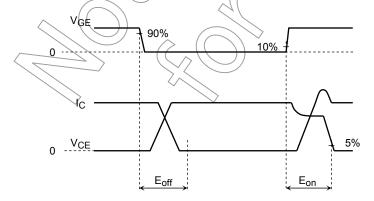
Cha	racteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GES}	V _{GE} = ±20 V, V _{CE} = 0	_	_	±500	nA
Collector cut-off	current	I _{CES}	V _{CE} = 600 V, V _{GE} = 0	_	_	1.0	mA
Gate-emitter cu	t-off voltage	V _{GE} (OFF)	I _C = 2 mA, V _{CE} = 5 V	3.5	_	6.5	V
Collector-emitte	r saturation voltage	V _{CE} (sat)	I _C = 20 A, V _{GE} = 15 V		2.0	2.45	V
Input capacitano	ce	C _{ies}	V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz	(F)	3000	-	pF
	Turn-on delay time	t _{d (on)}	, (7) 	0.06	-	
Switching time Rise time Turn-on time Turn-off delay time	Rise time	t _r	Inductive Load))	0.04	_	116
	Turn-on time	t _{on}		· –	0.17	_	
	t _{d (off)}	V _{CC} = 300 V, I _C = 20 A	_	0.24	_	μs	
	Fall time	t _f	$V_{GG} = +15 \text{ V}, R_G = 33 \Omega$	_	0.04	\nearrow	
	Turn-off time	t _{off}	(Note 1)	- (0.34	> -	
Switching loss	Turn-on switching loss	E _{on}	(Note 2)		0.40) –	mJ
Tu	Turn-off switching loss	E _{off}		7	0.43	ı	IIIJ
Peak forward vo	oltage	V _F	I _F = 20 A, V _{GE} = 0		_	2.1	V
Reverse recove	ry time	t _{rr}	I _F = 20 A, di/dt = -100 A/μs	\ -	100	_	ns

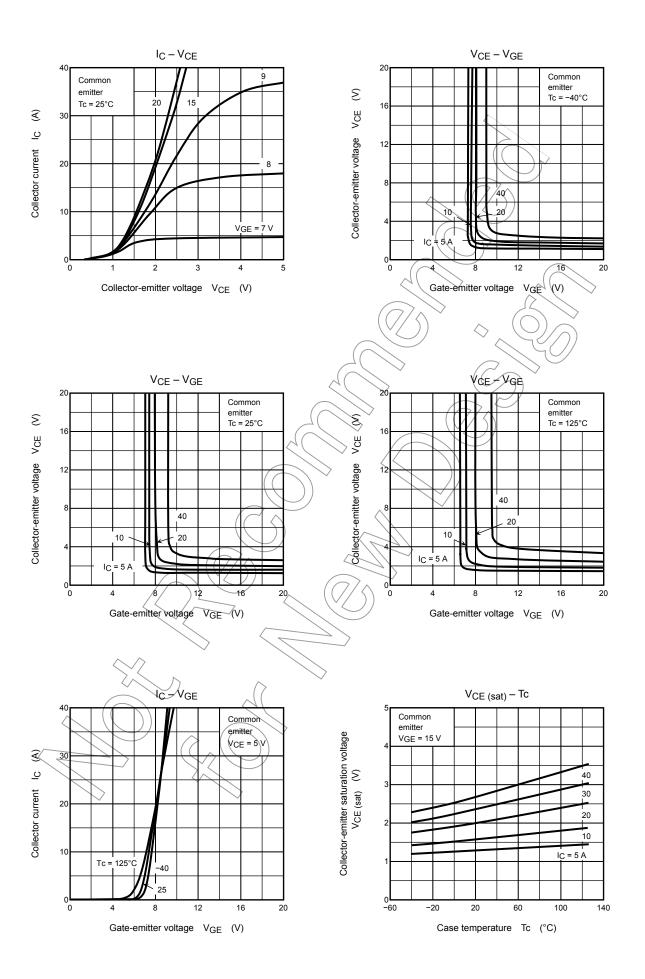
Note 1: Switching time measurement circuit and input/output waveforms

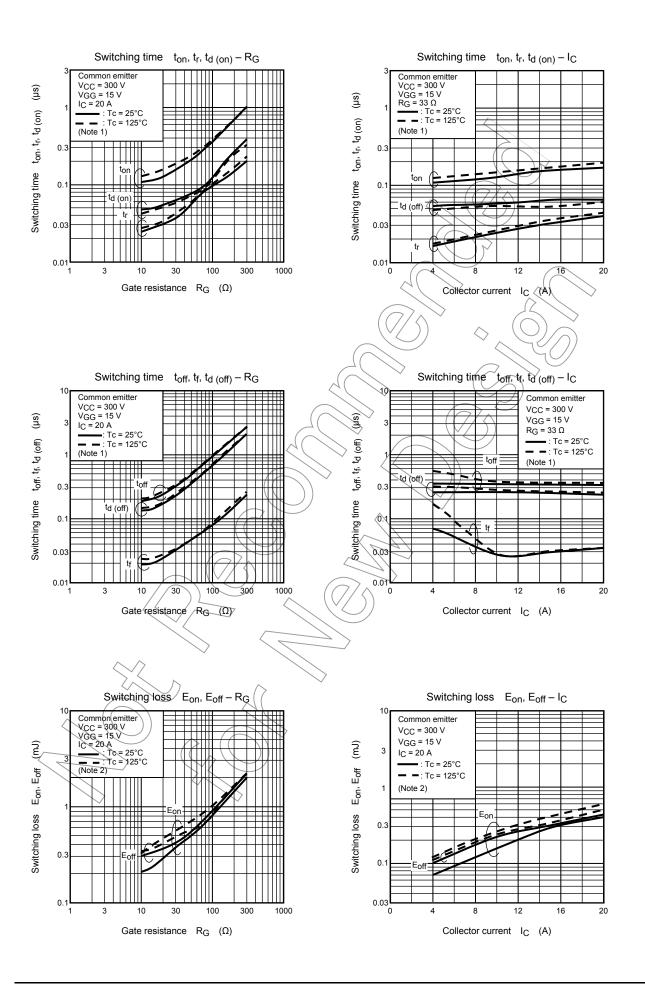


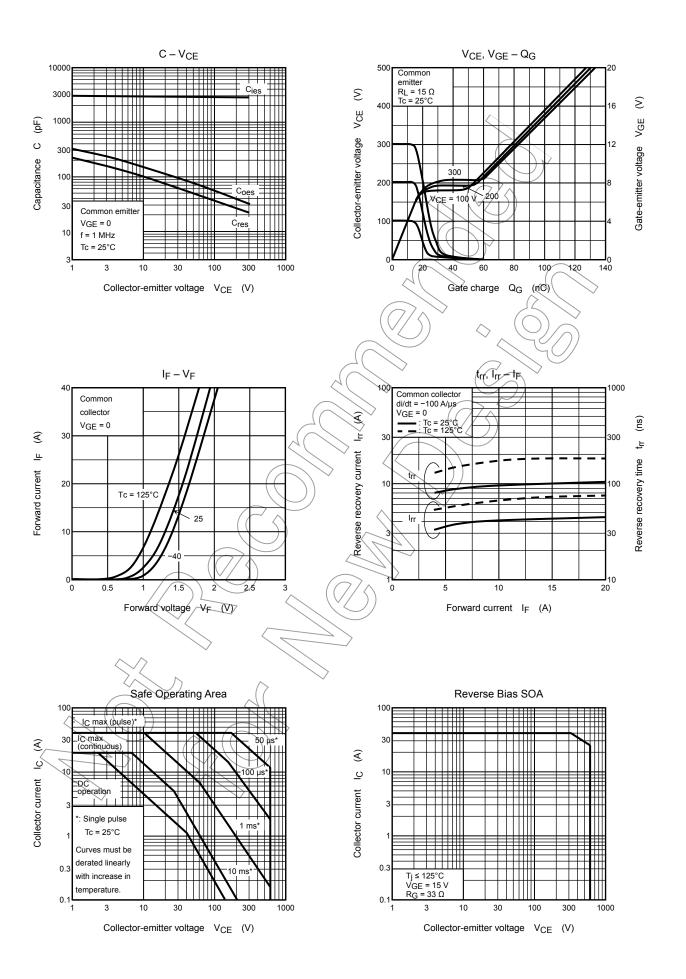
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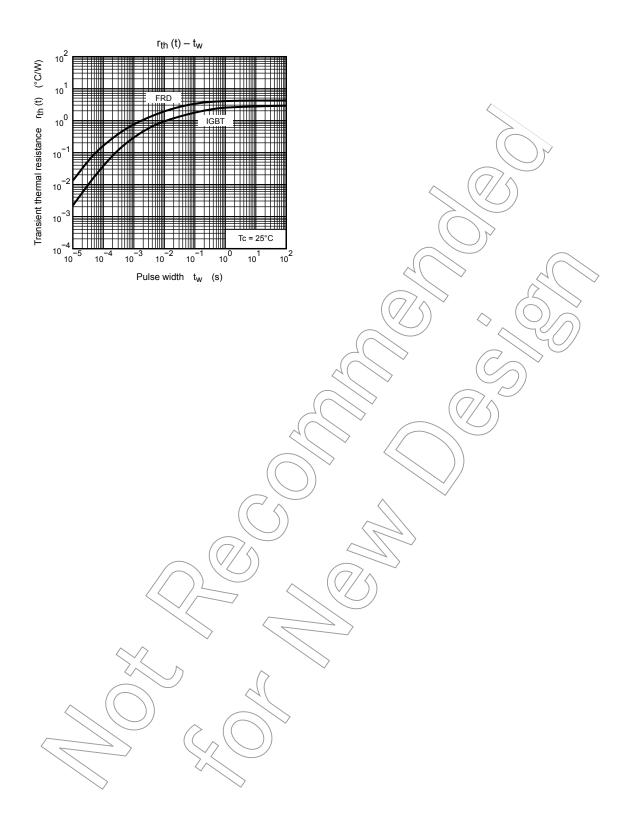
Note 2: Switching loss measurement waveforms











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